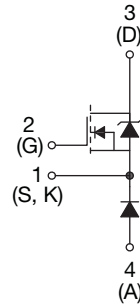


SOT-227 Power Module High Side Chopper - Power MOSFET, 100 A



SOT-227


FEATURES
MOSFET

- Enhanced body diode dV/dt and dI_F/dt capability
- Improved gate avalanche and dynamic dV/dt ruggedness
- Fully characterized capacitance and avalanche SOA
- Fully isolated package
- Easy to use and parallel
- Low on-resistance
- Simple drive requirements


**RoHS
COMPLIANT**
CHOPPER DIODE

- Low forward voltage drop
- Ultrafast, soft reverse recovery, with high operating junction temperature ($T_J \text{ max.} = 175^\circ\text{C}$)
- UL approved file E78996
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

PRIMARY CHARACTERISTICS	
MOSFET	
V_{DSS}	200 V
$R_{DS(on)}$	9.6 m Ω
I_D at 97 °C	80 A
Type	Modules - MOSFET
Package	SOT-227
CHOPPER DIODE	
I_F at 90 °C	64 A
t_{rr}	33 ns

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
MOSFET				
Drain to source voltage	V_{DSS}		200	V
Continuous drain current V_{GS} at 10 V	I_D	$T_C = 25^\circ\text{C}$	108	A
		$T_C = 90^\circ\text{C}$	83	
Pulsed drain current	$I_{DM}^{(1)}$		170	
Power dissipation	P_D	$T_C = 25^\circ\text{C}$	405	W
		$T_C = 90^\circ\text{C}$	229	
Gate to source voltage	V_{GS}		± 30	V
Single pulse avalanche energy	$E_{AS}^{(2)}$		600	mJ
Avalanche current	$I_{AR}^{(3)}$		50	A
Repetitive avalanche energy	$E_{AR}^{(3)}$		300	mJ
CHOPPER DIODE				
Cathode to anode voltage	V_R		200	V
Continuous forward current	I_F	$T_C = 25^\circ\text{C}$	92	A
		$T_C = 90^\circ\text{C}$	64	
Maximum peak one cycle non-repetitive surge current	I_{FSM}		280	A
Maximum power dissipation, chopper diode	P_D	$T_C = 90^\circ\text{C}$	79	W
MODULE				
Operating junction temperature range	T_J		-55 to +175	°C
Storage temperature range	T_{Stg}		-55 to +175	
RMS insulation voltage	V_{ISO}	Any terminal to case, $t = 1 \text{ min}$	2500	V

Notes

- (1) Repetitive rating; pulse width limited by maximum junction temperature starting $T_J = 25^\circ\text{C}$
- (2) Limited by $T_J \text{ max.}$, starting $T_J = 25^\circ\text{C}$, $L = 0.23 \text{ mH}$, $R_g = 25 \Omega$, $I_{AS} = 72 \text{ A}$, $V_{GS} = 10 \text{ V}$. Part not recommended for use above this value
- (3) Repetitive rating; pulse width limited by maximum junction temperature starting $T_J = 25^\circ\text{C}$, $L = 0.23 \text{ mH}$, $R_g = 25 \Omega$, $V_{GS} = 10 \text{ V}$, duty cycle 1 %



THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL		MIN.	TYP.	MAX.	UNITS
Junction to case thermal resistance	MOSFET	R _{thJC}		-	-	0.37	°C/W
	Chopper Diode			-	-	1.08	
Case to sink, flat greased surface (heatsink compound thermal conductivity = 1 W/mK)	Module	R _{thCS}		-	0.10	-	
Mounting torque			Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
			Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)
Approximate module weight				-	30	-	g

ELECTRICAL CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
MOSFET							
Drain-to-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 500 μA	200	-	-	V	
Breakdown voltage temperature coefficient	ΔV _{(BR)DSS} /ΔT _J	Reference to 25 °C, I _D = 1 mA	-	0.21	-	V/°C	
Static drain-to-source on-resistance	R _{DS(on)} ⁽¹⁾	V _{GS} = 10 V, I _D = 80 A	-	9.6	14.0	mΩ	
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.7	4.1	5.5	V	
		V _{DS} = V _{GS} , I _D = 250 μA, T _J = 125 °C	-	2.6	-		
Forward transconductance	g _{fs}	V _{DS} = 20 V, I _D = 80 A	-	200	-	S	
Drain-to-source leakage current	I _{DSS}	V _{DS} = 200 V, V _{GS} = 0 V	-	0.6	25	μA	
		V _{DS} = 200 V, V _{GS} = 0 V, T _J = 125 °C	-	20	500		
		V _{DS} = 200 V, V _{GS} = 0 V, T _J = 175 °C	-	1	5	mA	
Gate-to-source forward leakage	I _{GSS}	V _{GS} = 20 V	-	-	120	nA	
Gate-to-source reverse leakage		V _{GS} = -20 V	-	-	-120		
Total gate charge	Q _g	I _D = 80 A, V _{DS} = 100 V, V _{GS} = 10 V, see fig. 15 and fig. 28 ⁽¹⁾	-	161	-	nC	
Gate-to-source charge	Q _{gs}		-	54	-		
Gate-to-drain ("Miller") charge	Q _{gd}		-	52	-		
Turn-on delay time	t _{d(on)}	V _{DD} = 100 V, I _D = 80 A, R _g = 2.5 Ω, L = 500 μH	-	148	-	ns	
Rise time	t _r		-	215	-		
Turn-off delay time	t _{d(off)}		-	114	-		
Fall time	t _f		-	125	-		
Turn-on delay time	t _{d(on)}	V _{DD} = 100 V, I _D = 80 A, R _g = 2.5 Ω, L = 500 μH, T _J = 125 °C	-	132	-	ns	
Rise time	t _r		-	215	-		
Turn-off delay time	t _{d(off)}		-	124	-		
Fall time	t _f		-	108	-		
Internal source inductance	L _S	Between lead and center of die contact	-	3	-	nH	
Input capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 50 V, f = 1.0 MHz, see fig. 14	-	10 720	-	pF	
	C _{oss}		-	810	-		
	C _{rss}		-	160	-		
Drain to Case Capacitance	C _{d-cs}	V _{GS} = 0 V, (G-S shorted); f = 1 MHz	-	50	-		
CHOPPER DIODE							
Diode reverse breakdown voltage	V _{BR}	I _R = 100 μA	200	-	-	V	
Forward voltage drop	V _{FM}	I _F = 30 A	-	0.94	1.08		
		I _F = 30 A, T _J = 125 °C	-	0.8	-		
		I _F = 30 A, T _J = 175 °C	-	0.74	-		
Reverse leakage current	I _{RM}	V _R = V _R rated	-	1	50	μA	
		V _R = V _R rated, T _J = 125 °C	-	7	-		
		V _R = V _R rated, T _J = 175 °C	-	0.15	1	mA	
Junction capacitance	C _T	V _R = 200 V	-	119	-	pF	

Note

⁽¹⁾ Pulse width ≤ 400 μs, duty cycle ≤ 2 %



SOURCE-DRAIN RATINGS AND CHARACTERISTICS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
MOSFET						
Continuous source current (body diode)	I _S	MOSFET symbol showing the integral reverse p-n junction diode	-	-	108	A
Pulsed source current (body diode)	I _{SM} ⁽¹⁾		-	-	170	
Body diode forward voltage	V _{SD} ⁽²⁾	T _J = 25 °C, I _S = 80 A, V _{GS} = 0 V	-	0.88	1.02	V
		T _J = 125 °C, I _S = 80 A, V _{GS} = 0 V	-	0.76	-	
		T _J = 175 °C, I _S = 80 A, V _{GS} = 0 V	-	0.70	-	
Reverse recovery time	t _{rr}	T _J = 25 °C, I _F = 30 A, dI _F /dt = 100 A/μs, V _R = 100 V ⁽²⁾	-	145	-	ns
Reverse recovery current	I _{rr}		-	11	-	A
Reverse recovery charge	Q _{rr}		-	790	-	nC
Reverse recovery time	t _{rr}	T _J = 125 °C, I _F = 30 A, dI _F /dt = 100 A/μs, V _R = 100 V ⁽²⁾	-	170	-	ns
Reverse recovery current	I _{rr}		-	13.5	-	A
Reverse recovery charge	Q _{rr}		-	1140	-	nC
Forward turn-on time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS + LD)				

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
CHOPPER DIODE						
Reverse recovery time	t _{rr}	T _J = 25 °C, I _F = 30 A, dI _F /dt = 200 A/μs, V _R = 100 V ⁽²⁾	-	33	-	ns
Reverse recovery current	I _{rr}		-	3.5	-	A
Reverse recovery charge	Q _{rr}		-	59	-	nC
Reverse recovery time	t _{rr}	T _J = 125 °C, I _F = 30 A, dI _F /dt = 200 A/μs, V _R = 100 V ⁽²⁾	-	59	-	ns
Reverse recovery current	I _{rr}		-	8.3	-	A
Reverse recovery charge	Q _{rr}		-	238	-	nC

Notes

- (1) Repetitive rating, pulse width limited by maximum junction temperature (see fig. 27)
- (2) Pulse width ≤ 300 μs, duty cycle ≤ 2 %

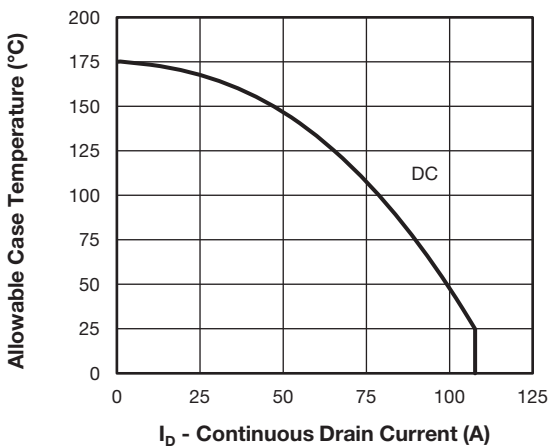


Fig. 1 - Maximum MOSFET Drain-Source Current vs. Case Temperature

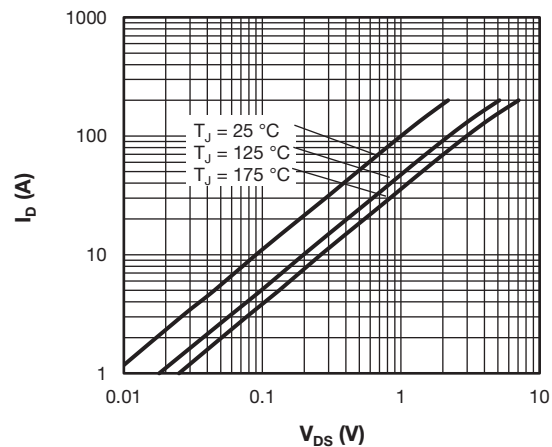


Fig. 2 - Typical MOSFET Output Characteristics, V_{GS} = 10 V

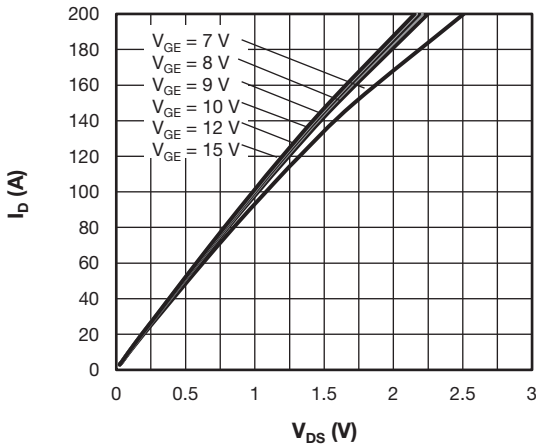


Fig. 3 - Typical MOSFET Output Characteristics, at $T_J = 25\text{ }^\circ\text{C}$

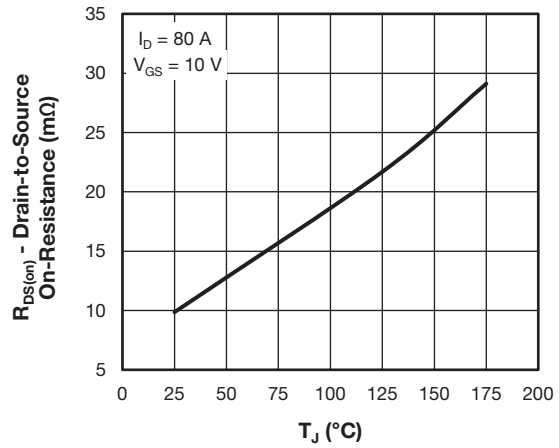


Fig. 6 - Typical Drain to Source On-Resistance vs. Temperature

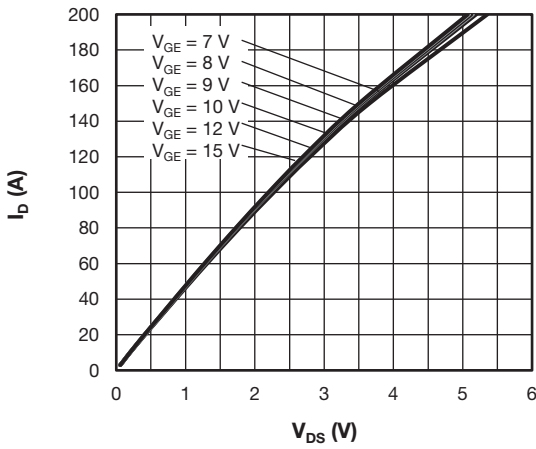


Fig. 4 - Typical MOSFET Output Characteristics, at $T_J = 125\text{ }^\circ\text{C}$

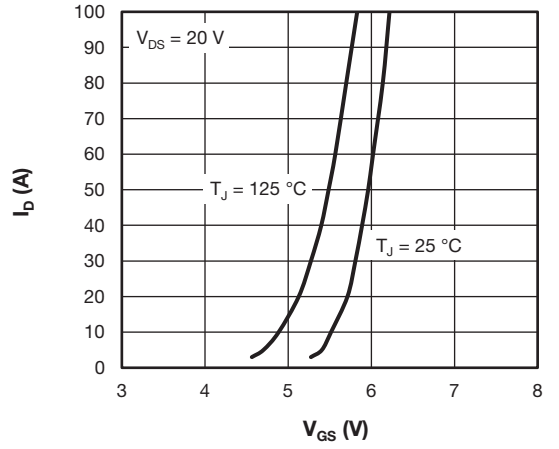


Fig. 7 - Typical MOSFET Transfer Characteristics

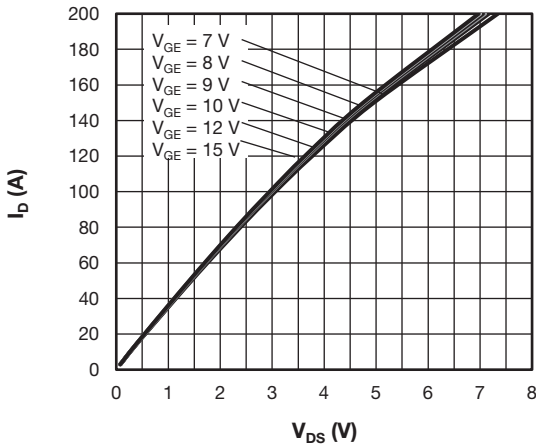


Fig. 5 - Typical MOSFET Output Characteristics, at $T_J = 175\text{ }^\circ\text{C}$

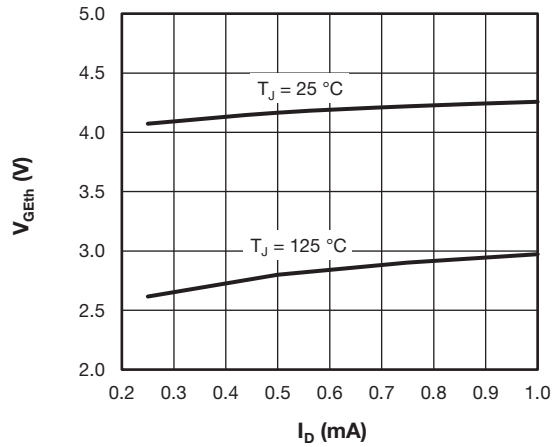


Fig. 8 - Typical MOSFET Gate Threshold Voltage

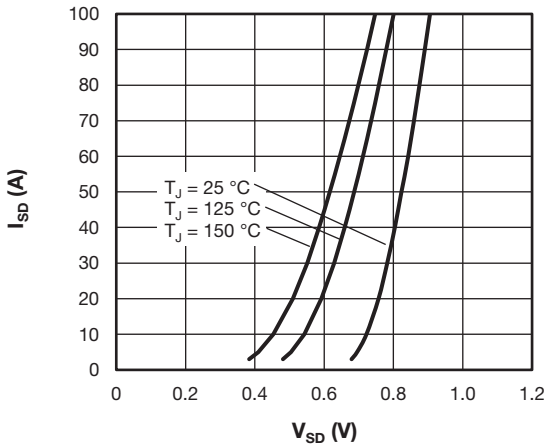


Fig. 9 - Typical MOSFET Body Diode Forward Current Characteristics

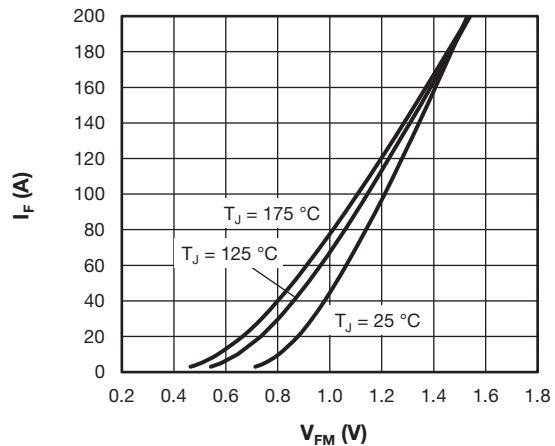


Fig. 12 - Typical Chopper Diode Forward Characteristics

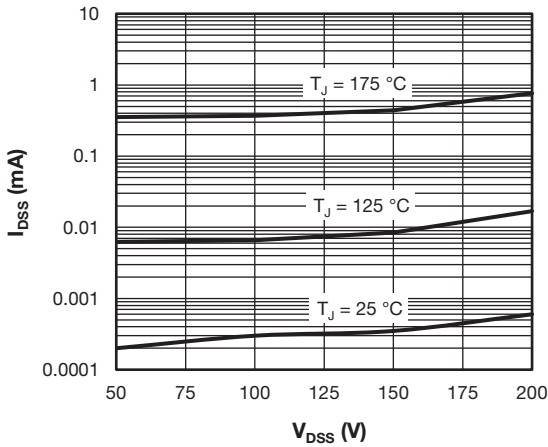


Fig. 10 - Typical MOSFET Zero Gate Voltage Drain Current

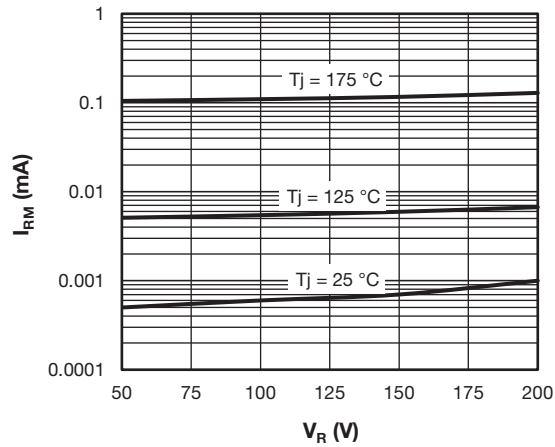


Fig. 13 - Typical Chopper Diode Reverse Leakage Current

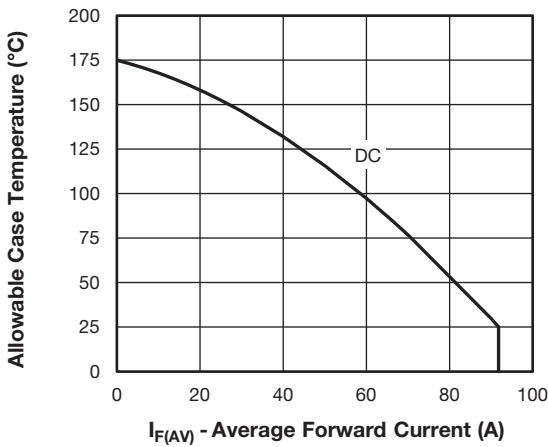


Fig. 11 - Maximum Allowable Forward Current vs. Case Temperature

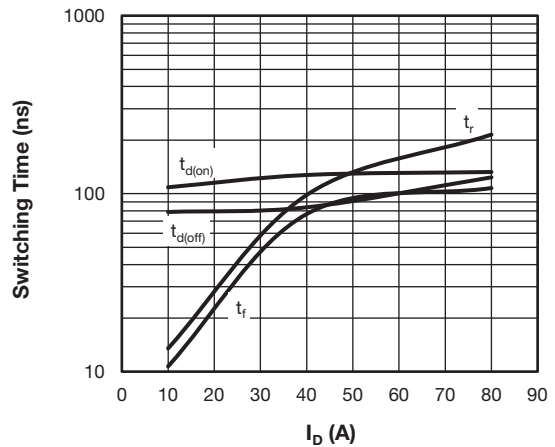


Fig. 14 - Typical MOSFET Switching Time vs. I_D
 $T_J = 125\text{ }^\circ\text{C}$, $V_{DD} = 100\text{ V}$, $R_g = 2.5\text{ }\Omega$, $V_{GS} = 10\text{ V}$, $L = 500\text{ }\mu\text{H}$

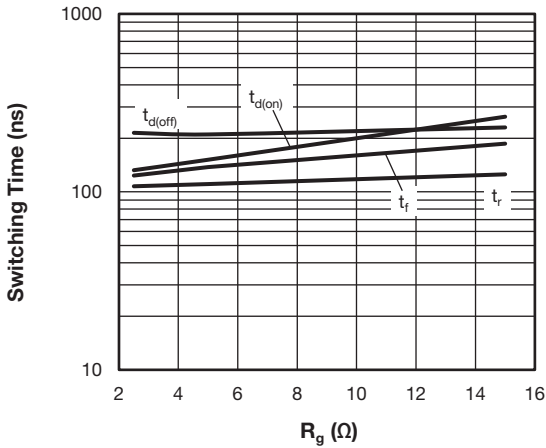


Fig. 15 - Typical MOSFET Switching Time vs. R_g
 $T_J = 125^\circ\text{C}$, $V_{DD} = 100\text{ V}$, $I_D = 80\text{ A}$, $L = 500\ \mu\text{H}$

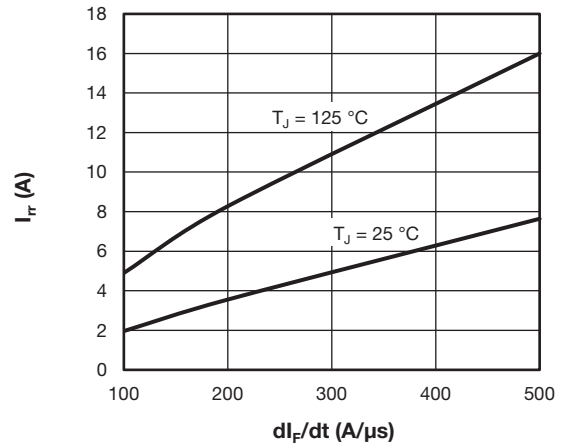


Fig. 17 - Typical Chopper Diode Reverse Recovery Current vs. di_F/dt
 $V_{rr} = 100\text{ V}$, $I_F = 30\text{ A}$

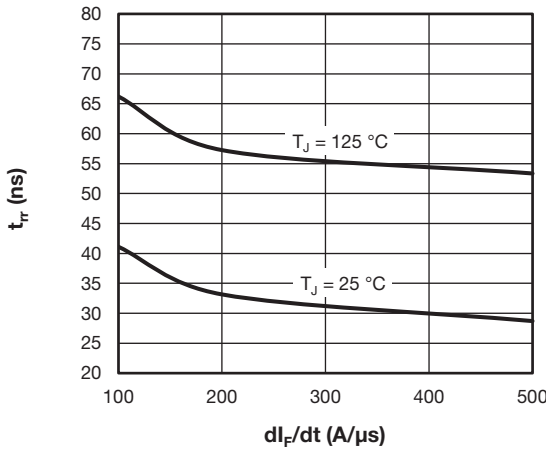


Fig. 16 - Typical Chopper Diode Reverse Recovery Time vs. di_F/dt
 $V_{rr} = 100\text{ V}$, $I_F = 30\text{ A}$

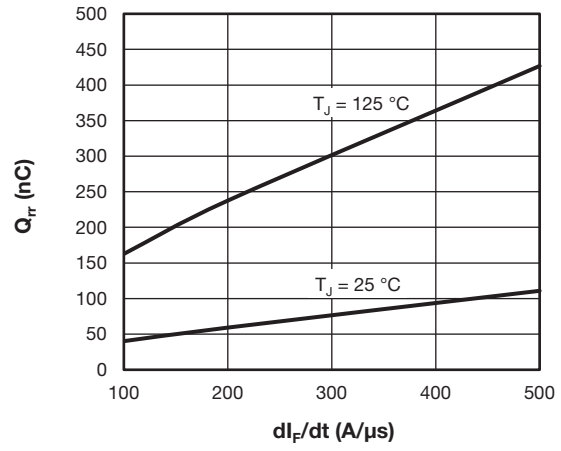


Fig. 18 - Typical Chopper Diode Reverse Recovery Charge vs. di_F/dt
 $V_{rr} = 100\text{ V}$, $I_F = 30\text{ A}$

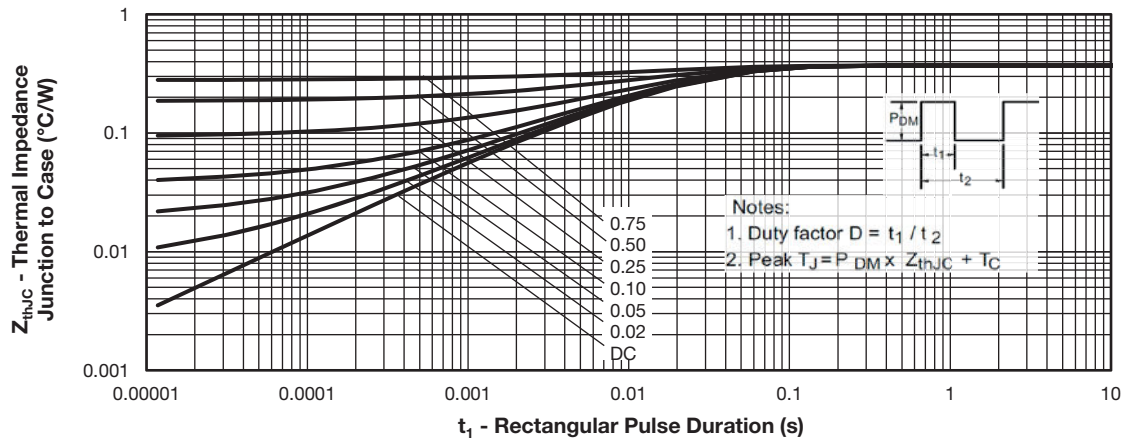


Fig. 19 - Maximum Thermal Impedance Z_{thJC} Characteristics - (MOSFET)

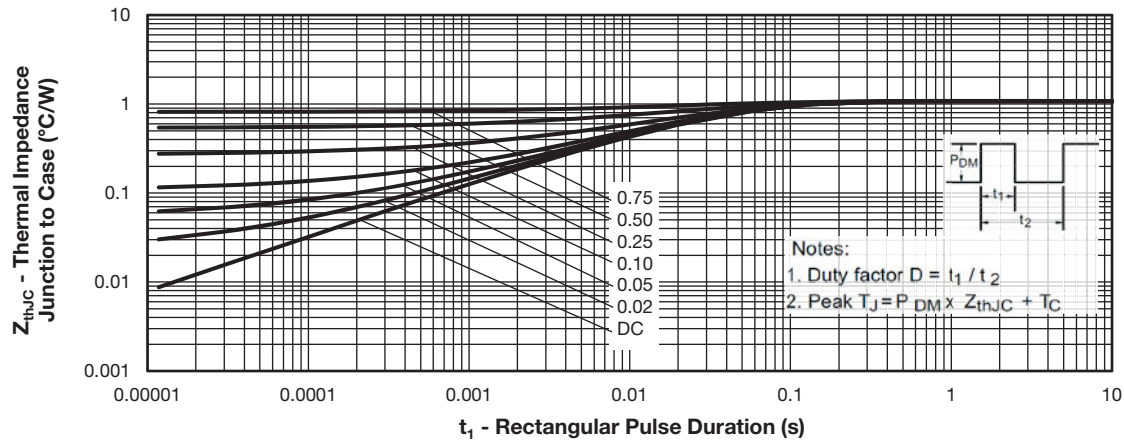
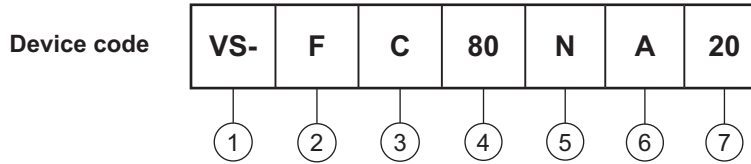


Fig. 20 - Maximum Thermal Impedance Characteristics (Chopper Diode)

CIRCUIT CONFIGURATION		
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
High side chopper	N	



ORDERING INFORMATION TABLE



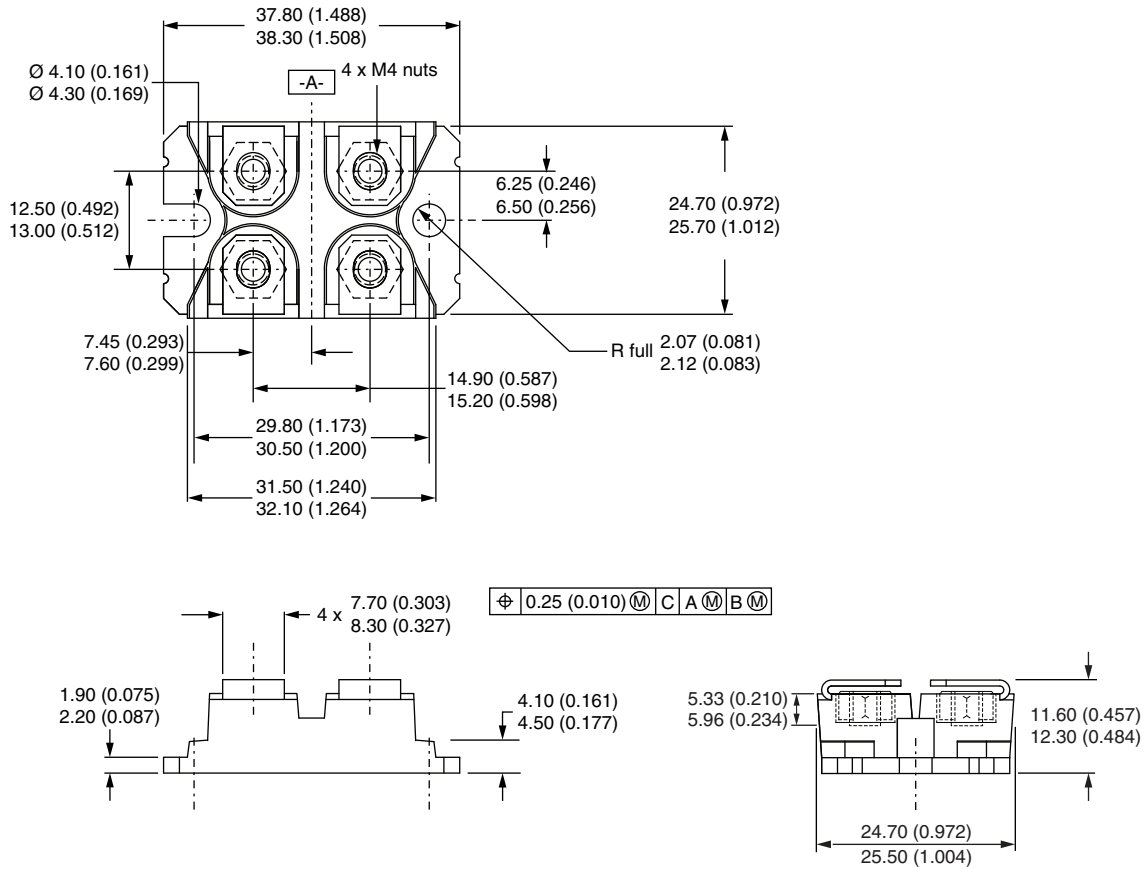
- 1** - Vishay Semiconductors product
- 2** - MOSFET module
- 3** - MOSFET die generation
- 4** - Current rating (80 = 80 A)
- 5** - N = high side chopper
- 6** - Package indicator SOT-227
- 7** - Voltage rating (20 = 200 V)

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95423
Packaging information	www.vishay.com/doc?95425



SOT-227 Generation 2

DIMENSIONS in millimeters (inches)



Note

- Controlling dimension: millimeter



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